

STANDARD RECOVERY DIODES

Stud Version

Features

- High surge current capability
- Designed for a wide range of applications
- Stud cathode and stud anode version
- Leaded version available
- Types up to 1600V V_{RRM}

40 A

Typical Applications

- Battery charges
- Converters
- Power supplies
- Machine tool controls

Major Ratings and Characteristics

Parameters	40HF(R)		Units
	10 to 120	140 to 160	
$I_{F(AV)}$	40	40	A
@ T_C	140	110	°C
$I_{F(RMS)}$	62		A
I_{FSM} @ 50Hz	570		A
@ 60Hz	595		A
I^2t @ 50Hz	1600		A ² s
@ 60Hz	1450		A ² s
V_{RRM} range	100 to 1200	1400 to 1600	V
T_J range	- 65 to 190	- 65 to 160	°C



case style
DO-203AB (DO-5)

40HF(R) Series

Bulletin I20201 rev. A 09/98

International
IOR Rectifier

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{RRM} , maximum repetitive peak reverse voltage V	V_{RSM} , maximum non-repetitive peak reverse voltage V	$V_{R(BR)}$, minimum avalanche voltage V (1)	I_{RRM} max. @ $T_J = T_J$ max. mA
40HF(R)	10	100	200	--	15
	20	200	300	--	
	40	400	500	500	
	60	600	720	725	9
	80	800	960	950	
	100	1000	1200	1150	
	120	1200	1440	1350	
	140	1400	1650	1550	4.5
	160	1600	1900	1750	

(1) Avalanche version only available from V_{RRM} 400V to 1600V.

Forward Conduction

Parameter		40HF(R)		Units	Conditions		
		10 to 120	140 to 160				
I _{F(AV)}	Max. average forward current @ Case temperature	40	40	A	180° conduction, half sine wave		
		140	110	°C			
I _{F(RMS)}	Max. RMS forward current	62		A			
P _R	Maximum non-repetitive peak reverse power	11		K · W	10μs square pulse, T _J = T _J max. see note (2)		
I _{FSM}	Max. peak, one-cycle forward, non-repetitive surge current	570	A	t = 10ms	No voltage	Sinusoidal half wave, Initial T _J = T _J max.	
		595		t = 8.3ms	reapplied		
		480		t = 10ms	100% V _{RRM}		
		500		t = 8.3ms	reapplied		
I ² t	Maximum I ² t for fusing	1600	A ² s	t = 10ms	No voltage		
		1450		t = 8.3ms	reapplied		
		1150		t = 10ms	100% V _{RRM}		
		1050		t = 8.3ms	reapplied		
I ² √t	Maximum I ² √t for fusing	16000		A ² √s	t = 0.1 to 10ms, no voltage reapplied		
V _{F(TO)1}	Low level value of threshold voltage	0.65		V	(16.7% × π × I _{F(AV)} < I < π × I _{F(AV)}), T _J = T _J max.		
V _{F(TO)2}	High level value of threshold voltage	0.70			(I > π × I _{F(AV)}), T _J = T _J max.		
r _{f1}	Low level value of forward slope resistance	4.29		mΩ	(16.7% × π × I _{F(AV)} < I < π × I _{F(AV)}), T _J = T _J max.		
r _{f2}	High level value of forward slope resistance	3.98			(I > π × I _{F(AV)}), T _J = T _J max.		
V _{FM}	Max. forward voltage drop	1.30		V	I _{pk} = 125A, T _J = 25°C, t _p = 400μs rectangular wave		

(2) Available only for Avalanche version, all other parameters the same as 40HF.

Thermal and Mechanical Specifications

Parameter		40HF(R)		Units	Conditions
		10 to 120	140 to 160		
T _J	Max. junction operating temperature range	-65 to 190	-65 to 160	°C	
T _{stg}	Max. storage temperature range	-65 to 190	-65 to 160		
R _{thJC}	Max. thermal resistance, junction to case	1.0		K/W	DC operation
R _{thCS}	Max. thermal resistance, case to heatsink	0.25			Mounting surface, smooth, flat and greased
T	Max. allowed mounting torque ±10%	2.3 - 3.4		Nm	Not lubricated threads
		20 - 30		lbf·in	
wt	Approximate weight	17 (0.6)		g (oz)	
Case style		DO-203AB (DO5)			See Outline Table

ΔR_{thJC} Conduction

(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.14	0.10	K/W	T _J = T _J max.
120°	0.16	0.17		
90°	0.21	0.22		
60°	0.30	0.31		
30°	0.50	0.50		

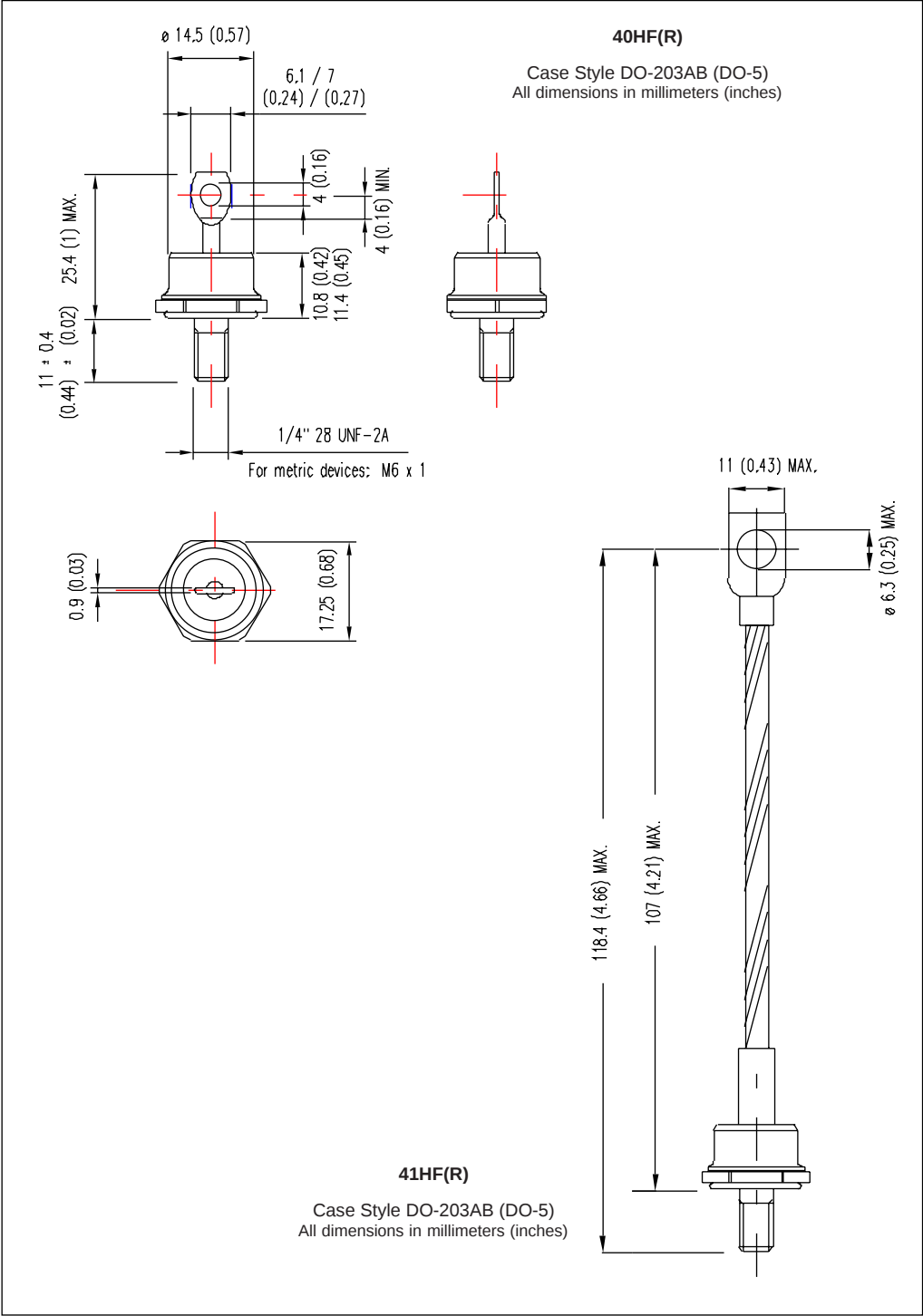
Ordering Information Table

Device Code				
	40	HF	R	160 M
	①	②	③	④ ⑤
1	- 40 = Standard device 41 = Not isolated lead 42 = Isolated lead with silicone sleeve (Red = Reverse polarity) (Blue = Normal polarity)			
2	- HF = Standard diode HA = Avalanche diode			
3	- None = Stud Normal Polarity (Cathode to Stud) R = Stud Reverse Polarity (Anode to Stud)			
4	- Voltage code: Code x 10 = V _{RRM} (See Voltage Ratings table)			
5	- None = Stud base DO-203AB (DO-5) 1/4" 28UNF-2A M = Stud base DO-203AB (DO-5) M6 X 1 - (Not available for Avalanche diodes)			

40HF(R) Series

Bulletin I20201 rev. A 09/98

Outlines Table



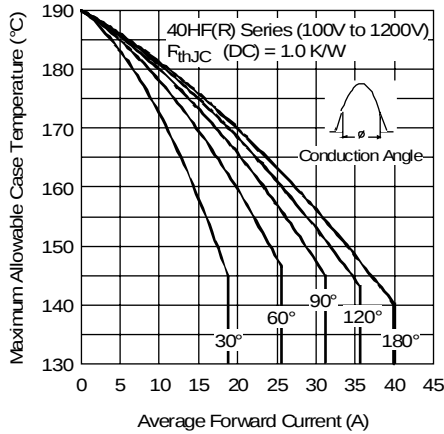


Fig. 1 - Current Ratings Characteristics

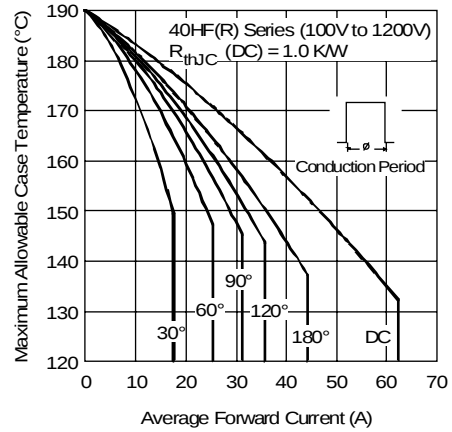


Fig. 2 - Current Ratings Characteristics

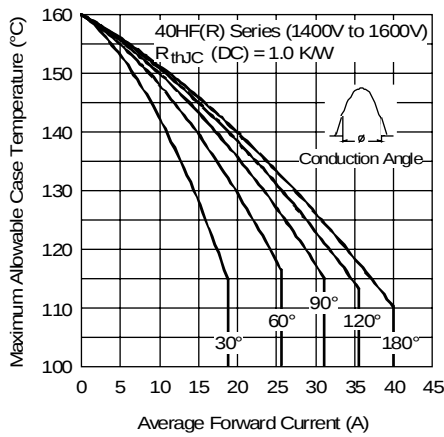


Fig. 3 - Current Ratings Characteristics

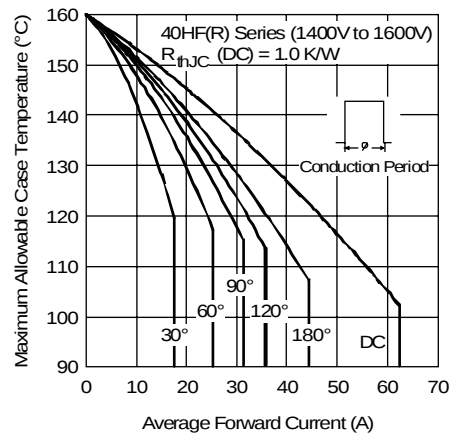


Fig. 4 - Current Ratings Characteristics

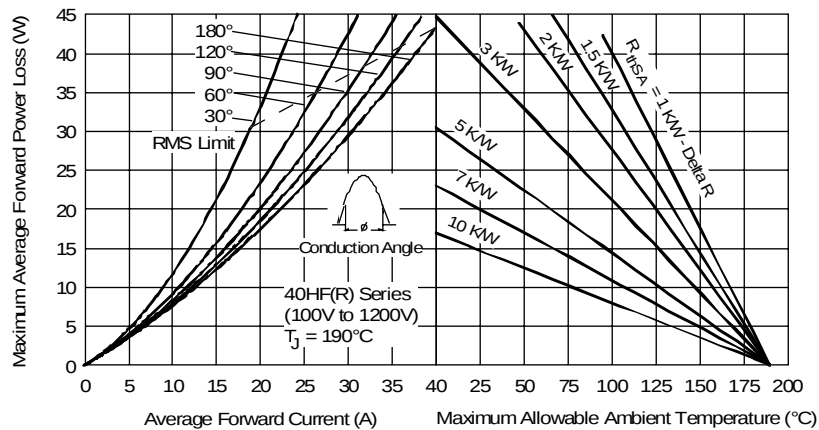


Fig. 5 - Forward Power Loss Characteristics

40HF(R) Series

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International
IR Rectifier

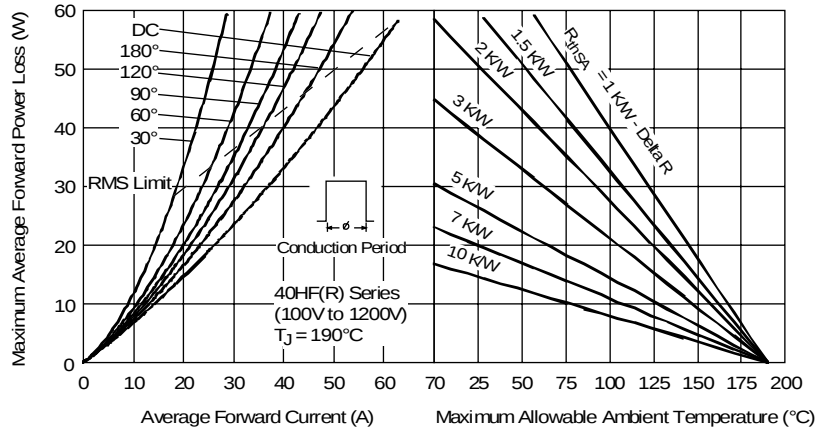


Fig. 6 - Forward Power Loss Characteristics

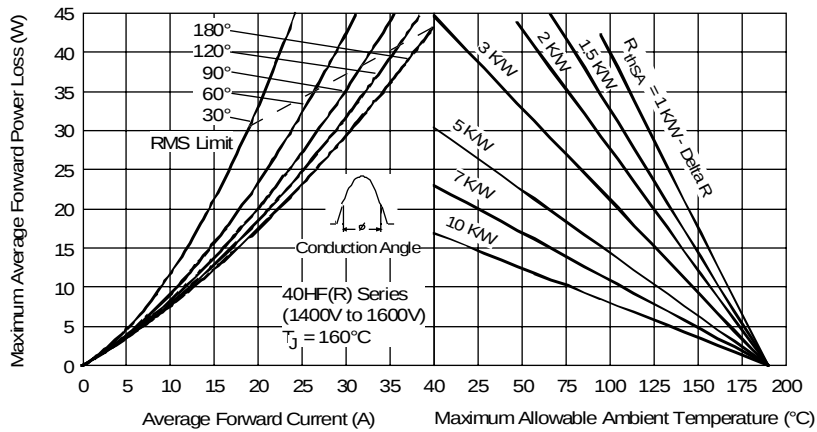


Fig. 7 - Forward Power Loss Characteristics

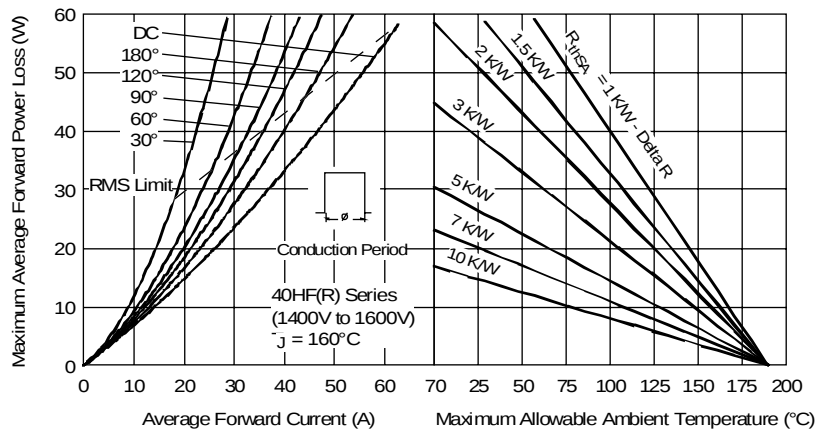


Fig. 8 - Forward Power Loss Characteristics

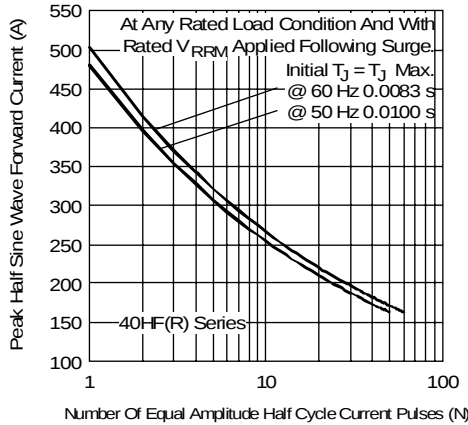


Fig. 9 - Maximum Non-Repetitive Surge Current

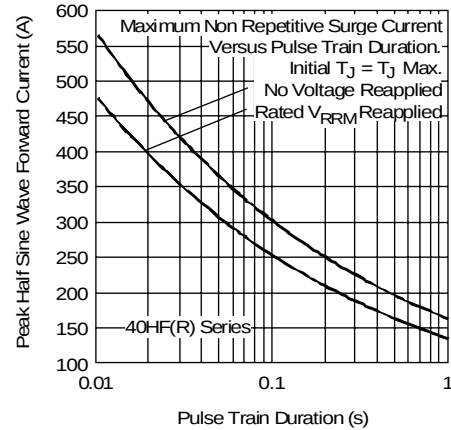


Fig. 10 - Maximum Non-Repetitive Surge Current

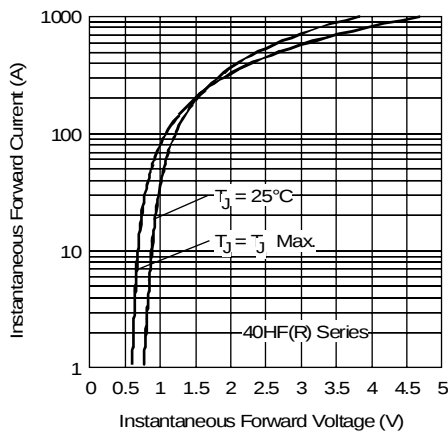


Fig. 11 - Forward Voltage Drop Characteristics

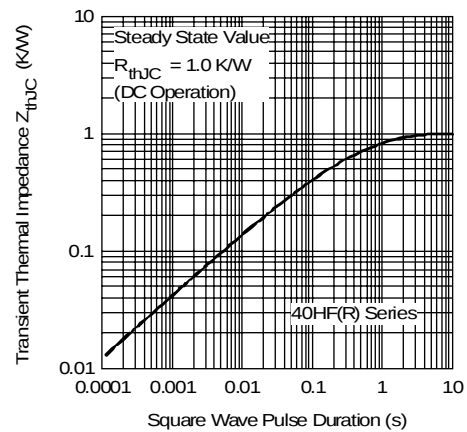


Fig. 12 - Thermal Impedance Z_{thJC} Characteristics



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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